

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

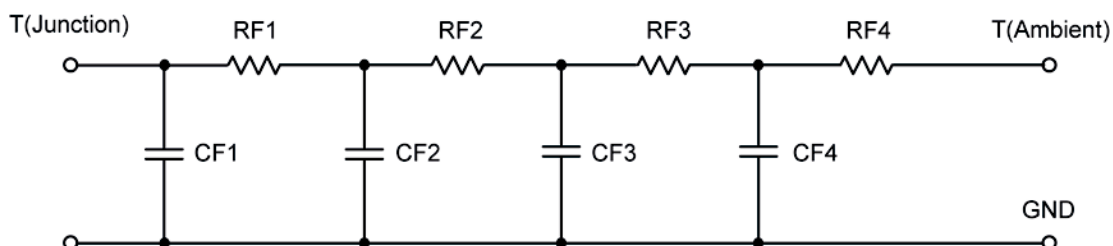
For a detailed explanation of implementing these values in P-Spice, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-Spice Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	12.4145	N/A	6.9005
RT2	5.5325	N/A	1.7114
RT3	17.9828	N/A	5.2205
RT4	47.9591	N/A	7.1734
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	51.6626 m	N/A	9.9576 m
CT2	3.8480 m	N/A	1.6896 m
CT3	95.4066 m	N/A	590.0730 m
CT4	1.2945	N/A	103.8321 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	7.1123	N/A	1.7297
RF2	21.6802	N/A	8.3335
RF3	11.9787	N/A	7.8025
RF4	43.3749	N/A	3.1510
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	3.9704 m	N/A	1.0495 m
CF2	27.4275 m	N/A	7.2549 m
CF3	182.3145 m	N/A	100.9652 m
CF4	1.2432	N/A	595.1445 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

